

BCR12PM-12LG

Triac

Medium Power Use

REJ03G1510-0100 Rev.1.00 Feb 14, 2007

Features

I_{T (RMS)}: 12 A
 V_{DRM}: 600 V

 $\bullet \quad I_{FGTI},\,I_{RGTI},\,I_{RGT\,III}\colon 30\;mA$

• V_{iso}: 2000V

• The Product guaranteed maximum junction temperature 150°C

• Insulated Type

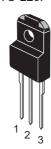
• Planar Type

• UL Recognized : Yellow Card No. E223904

File No.E80271

Outline

RENESAS Package code: PRSS0003AA-A (Package name: TO-220F)





- 1. T₁ Terminal
- 2. T₂ Terminal
- 3. Gate Terminal

Applications

Switching mode power supply, light dimmer, electronic switch, hair dryer, Television, Stereo system, refrigerator, Washing machine, infrared kotatsu, and carper, small motor controller, SS relay, solenoid driver, copying machine, electric tool, electric heater control, and other general purpose control applications

| Parameter | Symbol | Voltage class | Unit | |
|--|-----------|---------------|------|--|
| Farameter | Symbol | 12 | Onit | |
| Repetitive peak off-state voltage Note1 | V_{DRM} | 600 | V | |
| Non-repetitive peak off-state voltage ^{Note1} | V_{DSM} | 720 | V | |



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| Parameter | Symbol | Ratings | Unit | Conditions |
|--------------------------------|----------------------|-------------|------------------|--|
| RMS on-state current | I _{T (RMS)} | 12 | А | Commercial frequency, sine full wave 360°conduction, Tc = 92°C |
| Surge on-state current | I _{TSM} | 120 | Α | 60Hz sinewave 1 full cycle, peak value, non-repetitive |
| I ² t for fusion | l ² t | 60 | A ² s | Value corresponding to 1 cycle of half wave 60Hz, surge on-state current |
| Peak gate power dissipation | P_{GM} | 5 | W | |
| Average gate power dissipation | P _{G (AV)} | 0.5 | W | |
| Peak gate voltage | V_{GM} | 10 | V | |
| Peak gate current | I _{GM} | 2 | Α | |
| Junction Temperature | Tj | -40 to +150 | °C | |
| Storage temperature | Tstg | -40 to +150 | °C | |
| Mass | _ | 2.0 | g | Typical value |
| Isolation voltage | V _{iso} | 2000 | V | Ta = 25°C, AC 1 minute, $T_1 \bullet T_2 \bullet G$ terminal to case |

Notes: 1. Gate open.

Electrical Characteristics

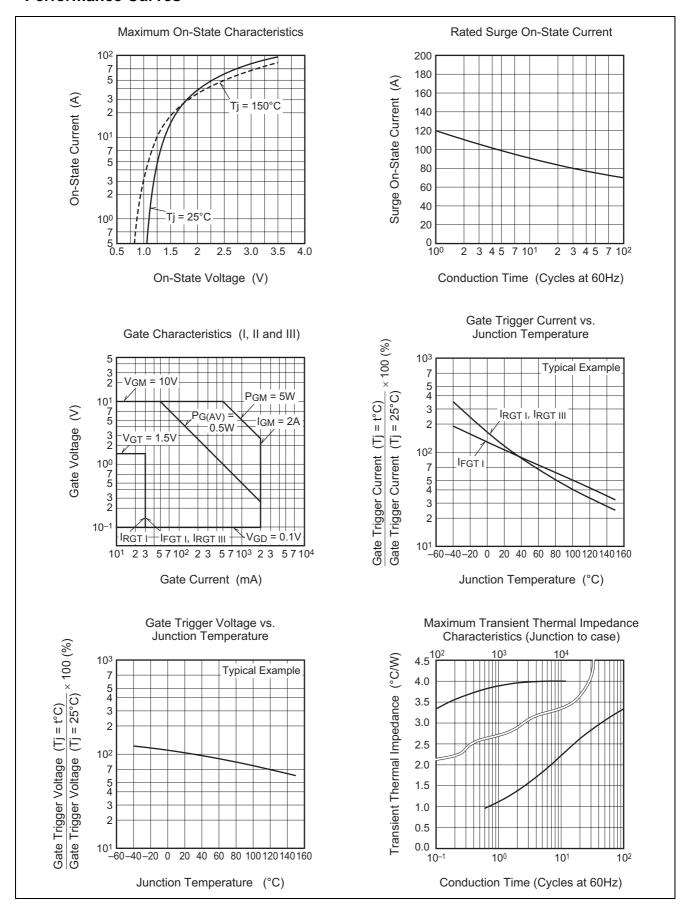
| Parameter | | Symbol | Min. | Тур. | Max. | Unit | Test conditions |
|---|-----|------------------------|---------|------|------|------|---|
| Repetitive peak off-state current | | I _{DRM} | _ | _ | 2.0 | mA | Tj = 150°C, V _{DRM} applied |
| On-state voltage | | V_{TM} | _ | _ | 1.6 | V | $Tc = 25^{\circ}C, I_{TM} = 20 A,$ |
| | | | | | | | instantaneous measurement |
| Gate trigger voltage ^{Note2} | I | $V_{FGT_{\mathrm{I}}}$ | | | 1.5 | V | $Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ Ω, |
| | II | $V_{RGT_{\mathrm{I}}}$ | | | 1.5 | V | $R_G = 330 \Omega$ |
| III | | $V_{RGT_{III}}$ | _ | _ | 1.5 | V | |
| Gate trigger curent ^{Note2} | I | I _{FGTI} | _ | _ | 30 | mA | $Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ Ω, |
| | II | I_{RGTI} | | | 30 | mA | $R_G = 330 \Omega$ |
| | III | I _{RGTIII} | _ | - | 30 | mA | |
| Gate non-trigger voltage | | V_{GD} | 0.2/0.1 | _ | _ | V | $Tj = 125^{\circ}C/150^{\circ}C, V_D = 1/2 V_{DRM}$ |
| Thermal resistance | | R _{th (j-c)} | _ | _ | 4.0 | °C/W | Junction to case ^{Note3} |
| Critical-rate of rise of off-state commutation voltage ^{Note4} | | (dv/dt)c | 10/1 | | _ | V/μs | Tj = 125°C/150°C |

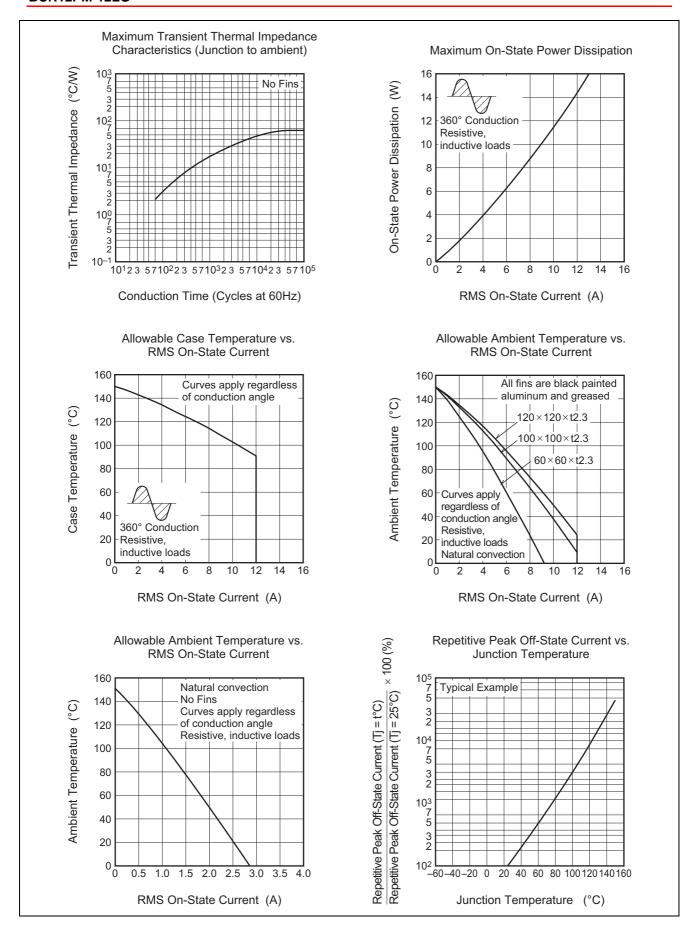
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

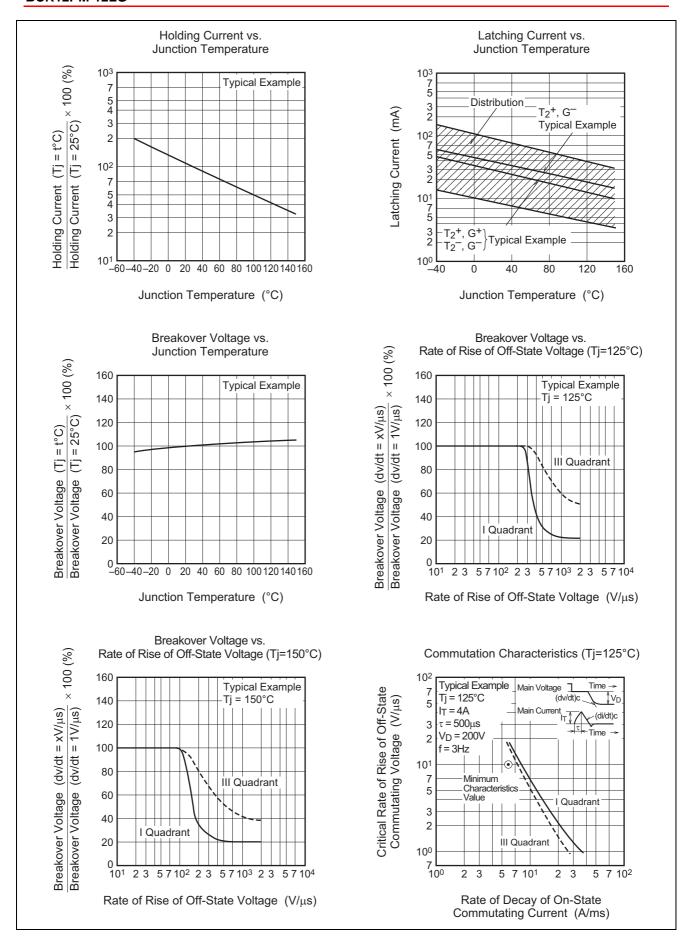
- 3. The contact thermal resistance $R_{th\,(j\text{-}c)}$ in case of greasing is 0.5°C/W.
- 4. Test conditions of the critical-rate of rise of off-state commutation voltage is shown in the table below.

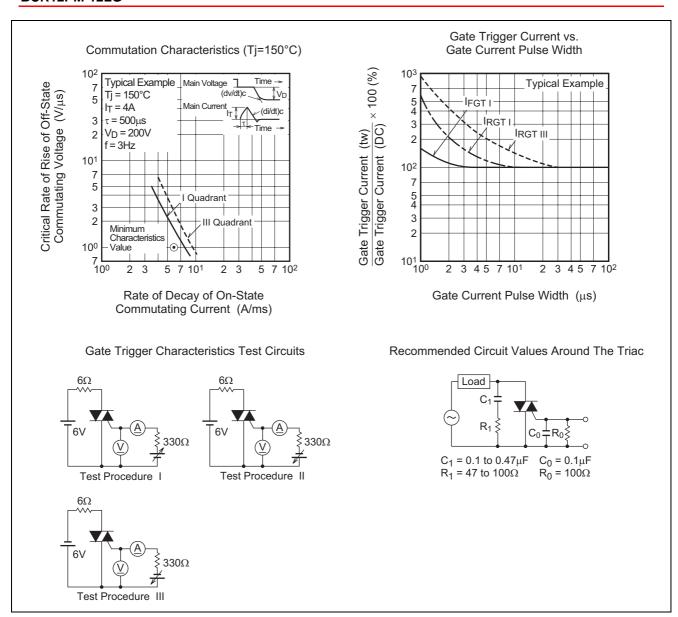
| Test conditions | Commutating voltage and current waveforms (inductive load) | | | |
|---|--|--|--|--|
| 1. Junction temperature Tj = 125°C/150°C | Supply Voltage → Time | | | |
| 2. Rate of decay of on-state commutating current (di/dt)c = -6.0 A/ms | Main Current (di/dt)c | | | |
| 3. Peak off-state voltage $V_D = 400 \text{ V}$ | Main Voltage — Time (dv/df)c | | | |

Performance Curves

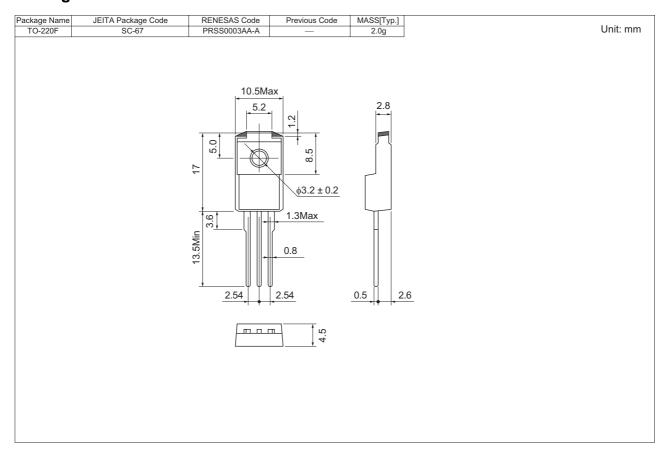








Package Dimensions



Order Code

| Lead form | Standard packing | Quantity | Standard order code | Standard order code example |
|---------------|-------------------------|----------|-------------------------------|-----------------------------|
| Straight type | Vinyl sack | 100 | Type name | BCR12PM-12LG |
| Lead form | Plastic Magazine (Tube) | 50 | Type name – Lead forming code | BCR12PM-12LG-A8 |

Note: Please confirm the specification about the shipping in detail.

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